

BDT63-A-B-C

SILICON DARLINGTON POWER TRANSISTORS

NPN epitaxial-base transistors in a monolithic Darlington circuit and housed in a TO-220 envelope. They are intended for output stages in audio equipment, general amplifiers, and analogue switching application.

PNP complements are BDT62-A-B-C

Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V_{CBO}	Collector-Base Voltage	BDT63	60	V
		BDT63A	80	
		BDT63B	100	
		BDT63C	120	
V_{CEO}	Collector-Emitter Voltage	BDT63	60	V
		BDT63A	80	
		BDT63B	100	
		BDT63C	120	
V_{EBO}	Emitter-Base Voltage	BDT63	5	V
		BDT63A		
		BDT63B		
		BDT63C		
I_C	Collector Current	BDT63	10	A
		BDT63A		
		BDT63B		
		BDT63C		
I_{CM}	Collector Peak Current	BDT63	15	A
		BDT63A		
		BDT63B		
		BDT63C		

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ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
I_B	Base Current		BDT63	250	mA
			BDT63A		
			BDT63B		
			BDT63C		
P_T	Power Dissipation	@ $T_{mb} < 25^\circ$	BDT63	90	W
			BDT63A		
			BDT63B		
			BDT63C		
T_J	Junction Temperature		BDT63	150	$^\circ\text{C}$
			BDT63A		
			BDT63B		
			BDT63C		
T_s	Storage Temperature range		BDT63	-65 to +150	
			BDT63A		
			BDT63B		
			BDT63C		

Limiting values in accordance with the Absolute Maximum System (IEC 134)

THERMAL CHARACTERISTICS

Symbol	Ratings		Value	Unit
R_{thJ-MB}	From junction to mounting base	BDT63	1.39	K/W
		BDT63A		
		BDT63B		
		BDT63C		
R_{thJ-A}	From junction to ambient in free air	BDT63	70	K/W
		BDT63A		
		BDT63B		
		BDT63C		

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)		Min	Typ	Max	Unit
I _{CBO}	Collector Cutoff Current	I _E = 0, V _{CB} = V _{CBO} max	BDT63	-	-	0.2	mA
			BDT63A				
			BDT63B				
			BDT63C				
		I _E = 0, V _{CB} =1/2 V _{CBO} max T _J = 150 °C	BDT63	-	-	2	mA
			BDT63A				
			BDT63B				
			BDT63C				
I _{CEO}	Collector Cutoff Current	I _E = 0, V _{CE} = 1/2 V _{CEO} max	BDT63	-	-	0.5	mA
			BDT63A				
			BDT63B				
			BDT63C				
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5 V, I _C = 0	BDT63	-	-	5.0	mA
			BDT63A				
			BDT63B				
			BDT63C				
V _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 30 mA, I _B = 0	BDT63	60	-	-	V
			BDT63A	80	-	-	
			BDT63B	100	-	-	
			BDT63C	120	-	-	
V _{CE(SAT)}	Collector-Emitter saturation Voltage (*)	I _C = 3 A, I _B = 12 mA	BDT63	-	-	2	V
			BDT63A				
			BDT63B				
			BDT63C				
		I _C = 8 A, I _B =80 mA	BDT63	-	-	2.5	
			BDT63A				
			BDT63B				
			BDT63C				

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings			Min	Typ	Max	Unit
$V_{BE(on)}$	Base-Emitter Voltage (*)	$I_C= 3\text{ A}$, $V_{CE}= 3\text{ V}$	BDT63	-	-	2.5	V
			BDT63A				
			BDT63B				
			BDT63C				
h_{FE}	DC Current Gain (*)	$V_{CE}= 3.0\text{ V}$, $I_C= 3\text{ A}$	BDT63	1000	-	-	-
			BDT63A				
			BDT63B				
			BDT63C				
		$V_{CE}= 3.0\text{ V}$, $I_C= 10\text{ A}$	BDT63	-	3000	-	
			BDT63A				
			BDT63B				
			BDT63C				
V_{ECF}	C-E Diode Forward Voltage	$I_F= 3\text{ A}$	BDT63	-	-	2	V
			BDT63A				
			BDT63B				
			BDT63C				
C_{OB}	Output Capacitance	$I_E= 0$, $V_{CB}= 10\text{ V}$ $f_{test}= 1\text{ MHz}$	BDT63	-	100	-	pF
			BDT63A				
			BDT63B				
			BDT63C				

SWITCHING TIMES

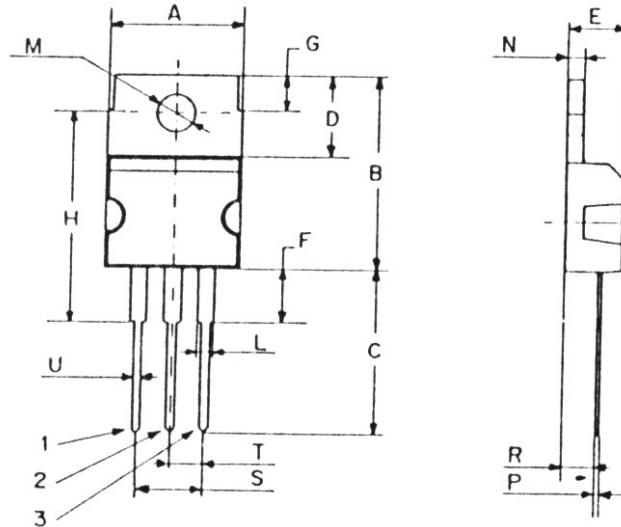
Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
t_{on}	turn-on time	$I_C = 3\text{ A}$, $V_{CC} = 10\text{ V}$ $I_{B1} = -I_{B2} = 12\text{ mA}$	-	1	2.5	μs
t_{off}	turn-off time		-	5	10	

(*) Pulse Width $\approx 300\text{ }\mu\text{s}$, Duty Cycle $\angle 2.0\%$

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MECHANICAL DATA CASE TO-220

DIMENSIONS (mm)		
	Min.	Max.
A	9,90	10,30
B	15,65	15,90
C	13,20	13,40
D	6,45	6,65
E	4,30	4,50
F	2,70	3,15
G	2,60	3,00
H	15,75	17,15
L	1,15	1,40
M	3,50	3,70
N	-	1,37
P	0,46	0,55
R	2,50	2,70
S	4,98	5,08
T	2,49	2,54
U	0,70	0,90



Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Package	Collector

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